

Kyung Jean Yoon

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

36 papers	1,613 citations	20 h-index	38 g-index
38 ext. papers	1,787 ext. citations	8.4 avg, IF	4.4 L-index

#	Paper	IF	Citations
36	In-Memory Hamming Error-Correcting Code in Memristor Crossbar. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-8	2.9	1
35	In-Memory Stateful Logic Computing Using Memristors: Gate, Calculation, and Application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021 , 15, 2100208	2.5	8
34	Weight Update Generation Circuit Utilizing Phase Noise of Integrated Complementary MetalOxideSemiconductor Ring Oscillator for Memristor Crossbar Array Neural Network-Based Stochastic Learning. <i>Advanced Intelligent Systems</i> , 2020 , 2, 2000011	6	1
33	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. <i>Advanced Intelligent Systems</i> , 2020 , 2, 1900082	6	19
32	What Will Come After V-NAND? Vertical Resistive Switching Memory?. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800914	6.4	38
31	Single-Cell Stateful Logic Using a Dual-Bit Memristor. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1800629	2.5	17
30	Fabrication of a Cu-Cone-Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. <i>Advanced Functional Materials</i> , 2019 , 29, 1806278	15.6	33
29	Nociceptive Memristor. <i>Advanced Materials</i> , 2018 , 30, 1704320	24	69
28	Fully Functional Logic-In-Memory Operations Based on a Reconfigurable Finite-State Machine Using a Single Memristor. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800189	6.4	26
27	Filament Shape Dependent Reset Behavior Governed by the Interplay between the Electric Field and Thermal Effects in the Pt/TiO ₂ /Cu Electrochemical Metallization Device. <i>Advanced Electronic Materials</i> , 2017 , 3, 1600404	6.4	20
26	Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 ⁹ . <i>Advanced Electronic Materials</i> , 2017 , 3, 1700152	6.4	35
25	Comparison of the Atomic Layer Deposition of Tantalum Oxide Thin Films Using Ta(NBu)(NEt), Ta(NBu)(NEt)Cp, and HO. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 537-547	9.5	13
24	Next-Generation Memory: Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 ⁹ (Adv. Electron. Mater. 7/2017). <i>Advanced Electronic Materials</i> , 2017 , 3,	6.4	1
23	A study of the transition between the non-polar and bipolar resistance switching mechanisms in the TiN/TiO ₂ /Al memory. <i>Nanoscale</i> , 2016 , 8, 16455-66	7.7	18
22	Uniform Self-rectifying Resistive Switching Behavior via Preformed Conducting Paths in a Vertical-type Ta ₂ O ₅ /HfO _{2-x} Structure with a Sub-10 ² Cell Area. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 18215-21	9.5	24
21	A crossbar resistance switching memory readout scheme with sneak current cancellation based on a two-port current-mode sensing. <i>Nanotechnology</i> , 2016 , 27, 485201	3.4	19
20	Resistance switching behavior of atomic layer deposited SrTiO ₃ film through possible formation of Sr ₂ Ti ₆ O ₁₃ or Sr ₁ Ti ₁₁ O ₂₀ phases. <i>Scientific Reports</i> , 2016 , 6, 20550	4.9	16

19	Comprehensive Writing Margin Analysis and its Application to Stacked one Diode-One Memory Device for High-Density Crossbar Resistance Switching Random Access Memory. <i>Advanced Electronic Materials</i> , 2016 , 2, 1600326	6.4	31
18	Interface engineering for improving reliability of resistance switching in Cu/HfO ₂ /TiO ₂ /Pt structure. <i>Applied Physics Letters</i> , 2015 , 107, 072901	3.4	12
17	Pt/Ta ₂ O ₅ /HfO ₂ -x/Ti resistive switching memory competing with multilevel NAND flash. <i>Advanced Materials</i> , 2015 , 27, 3811-6	24	134
16	Electronic resistance switching in the Al/TiO(x)/Al structure for forming-free and area-scalable memory. <i>Nanoscale</i> , 2015 , 7, 11063-74	7.7	63
15	Highly Uniform, Electroforming-Free, and Self-Rectifying Resistive Memory in the Pt/Ta ₂ O ₅ /HfO ₂ -x/TiN Structure. <i>Advanced Functional Materials</i> , 2014 , 24, 5086-5095	15.6	157
14	Evolution of the shape of the conducting channel in complementary resistive switching transition metal oxides. <i>Nanoscale</i> , 2014 , 6, 2161-9	7.7	34
13	A Review of Three-Dimensional Resistive Switching Cross-Bar Array Memories from the Integration and Materials Property Points of View. <i>Advanced Functional Materials</i> , 2014 , 24, 5316-5339	15.6	259
12	Highly improved uniformity in the resistive switching parameters of TiO ₂ thin films by inserting Ru nanodots. <i>Advanced Materials</i> , 2013 , 25, 1987-92	24	152
11	Ionic bipolar resistive switching modes determined by the preceding unipolar resistive switching reset behavior in Pt/TiO ₂ /Pt. <i>Nanotechnology</i> , 2013 , 24, 145201	3.4	18
10	Control of conducting filaments in TiO ₂ films by a thin interfacial conducting oxide layer at the cathode. <i>Applied Physics Letters</i> , 2013 , 102, 082903	3.4	7
9	Titanium dioxide thin films for next-generation memory devices. <i>Journal of Materials Research</i> , 2013 , 28, 313-325	2.5	56
8	32 B ₂ Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. <i>Advanced Functional Materials</i> , 2013 , 23, 1440-1449	15.6	136
7	Resistive Memory: 32 B ₂ Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory (Adv. Funct. Mater. 11/2013). <i>Advanced Functional Materials</i> , 2013 , 23, 1350-1350	15.6	2
6	Substrate Dependent Growth Behaviors of Plasma-Enhanced Atomic Layer Deposited Nickel Oxide Films for Resistive Switching Application. <i>Chemistry of Materials</i> , 2012 , 24, 4675-4685	9.6	33
5	Optimization of chemical structure of Schottky-type selection diode for crossbar resistive memory. <i>ACS Applied Materials & Interfaces</i> , 2012 , 4, 5338-45	9.5	9
4	Memristive tri-stable resistive switching at ruptured conducting filaments of a Pt/TiO ₂ /Pt cell. <i>Nanotechnology</i> , 2012 , 23, 185202	3.4	62
3	Schottky diode with excellent performance for large integration density of crossbar resistive memory. <i>Applied Physics Letters</i> , 2012 , 100, 213508	3.4	30
2	Improved endurance of resistive switching TiO ₂ thin film by hourglass shaped Magn ₂ filaments. <i>Applied Physics Letters</i> , 2011 , 98, 262901	3.4	60

1 Poster: Memristive Systems523-587